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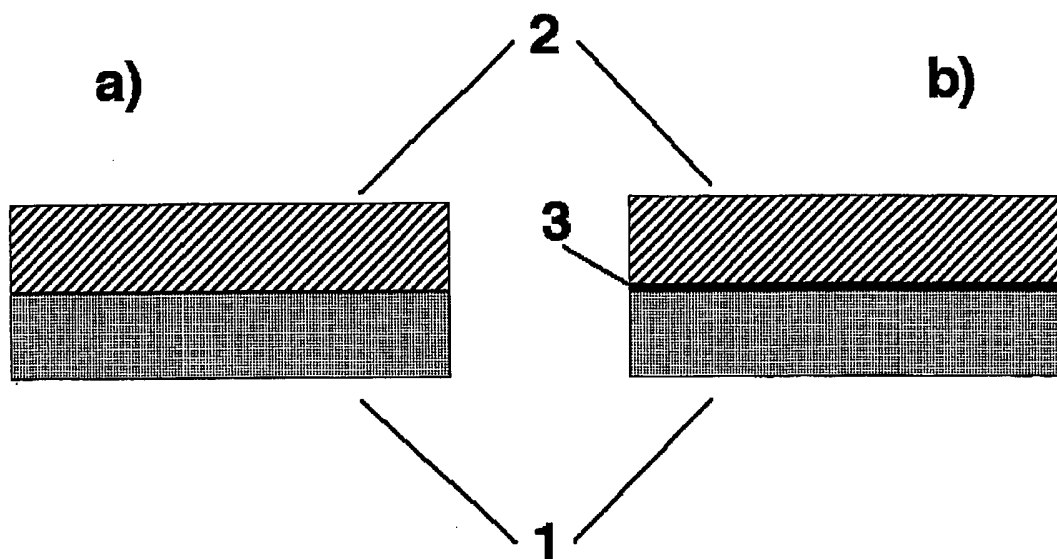
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(54) Title: ADHESION LAYER FOR THIN FILM TRANSISTORS



(57) Abstract: A method for manufacturing a poly- or microcrystalline silicon layer on an insulator comprises a silicon containing insulator, growing a thin adhesion promoting layer comprising amorphous silicon onto it and further growing a poly- or microcrystalline silicon layer onto the adhesion promoting layer. Such a sequence of layers, deposited with a PECVD method, shows good adhesion of the poly- or microcrystalline silicon on the base and is advantageous in the production of semiconductors, such as thin film transistors.

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INTERNATIONAL SEARCH REPORT

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A. CLASSIFICATION OF SUBJECT MATTER

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B. FIELDS SEARCHED

Minimum documentation searched (classification system followed by classification symbols)

C23C

Documentation searched other than minimum documentation to the extent that such documents are included in the fields searched

Electronic data base consulted during the international search (name of data base and, where practical, search terms used)

EPO-Internal

C. DOCUMENTS CONSIDERED TO BE RELEVANT

Category *	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
X	P. ROCA I CABARROCAS: "MICROCRYSTALLINE SILICON: AN EMERGING MATERIAL FOR STABLE THIN-FILM TRANSISTORS." JOURNAL OF THE SID, vol. 12, no. 1, 1 March 2004 (2004-03-01), pages 3-9, XP008058508 US	1-3, 5-8, 11
Y	cited in the application paragraph '0002!; figure 1 ----- -/--	9, 10



Further documents are listed in the continuation of box C.



Patent family members are listed in annex.

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C.(Continuation) DOCUMENTS CONSIDERED TO BE RELEVANT		
Category °	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
X	I.D. FRENCH ET AL: "Microcrystalline Si TFTs for integrated multiplexers and shift registers" SID CONFERENCE RECORD OF THE INTERNATIONAL DISPLAY RESEARCH CONFERENCE, 1 January 2001 (2001-01-01), pages 367-370, XP008058418 JP page 367, right-hand column, line 1 - line 14; figure 1 -----	1,4,8,11
Y	US 2004/035822 A1 (TSUMORI TOSHIHIRO ET AL) 26 February 2004 (2004-02-26) paragraph '0025! -----	9
Y	S. VEPREK ET AL: "Parameters controlling the deposition of amorphous and microcrystalline silicon in Si/H discharge plasmas" JOURNAL DE PHYSIQUE COLLOQUE, vol. 42, no. c-4, 1 October 1981 (1981-10-01), pages 251-255, XP008058542 fr abstract -----	10

Information on patent family members

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